

Please amend the present application as follows:

Claims

The following is a copy of Applicant's claims that identifies language being added with underlining ("___") and language being deleted with strikethrough ("—"), as is applicable:

1. (Previously presented) A system comprising:
a two-terminal drain-gate-connected modified flash cell having no erasing circuitry; and
an ultraviolet (UV) light window adapted to expose the high-density non-volatile fast memory to UV light.
- 2-3. (Canceled)
4. (Previously presented) The system of claim 1, wherein the two-terminal drain-gate-connected modified flash cell is a diode-connected nitrided read-only memory (NROM) cell.
5. (Original) A device comprising:
two-terminal drain-gate-connected modified flash cells having no erasing circuitry; and
an ultraviolet (UV) light window adapted to expose the two-terminal drain-gate-connected modified flash cells to UV light.

6. (Original) The device of claim 5, wherein the two-terminal drain-gate-connected modified flash cells are configured as a two-dimensional planar matrix of cells.

7. (Original) The device of claim 6, wherein the two-dimensional planar matrix of cells is a NAND configuration.

8. (Original) The device of claim 6, wherein the two-dimensional planar matrix of cells is a NOR configuration.

9. (Original) The device of claim 5, wherein the two-terminal drain-gate-connected modified flash cells are configured as three-dimensional layers.

10. (Previously presented) A system comprising:
two-terminal drain-gate-connected modified flash cells having no erasing circuitry; and
an ultraviolet (UV) light window adapted to expose the modified flash cells to UV light.

11. (Original) The system of claim 10, wherein the UV light window is located above a control gate of the modified flash cells.

12. (Original) The system of claim 10, wherein the UV light window is located below a substrate of the modified flash cells.

13. (Original) The system of claim 10, wherein the UV light window is interposed between control gates of the modified flash cells.

14. (Original) The system of claim 10, wherein the UV light window is offset from control gates of the modified flash cells.

15. (Original) The system of claim 10, wherein the UV light window is adapted to diffuse UV light entering the UV light window.

16. (Original) The system of claim 10, wherein the modified flash cells are arranged in a NAND configuration.

17. (Original) The system of claim 10, wherein the modified flash cells are arranged in a NOR configuration.

18. (Original) The system of claim 10, wherein the modified flash cells are configured as a two-dimensional planar matrix of cells.

19. (Original) The system of claim 18, wherein the two-dimensional planar matrix of cells is a NAND configuration.

20. (Original) The system of claim 18, wherein the two-dimensional planar matrix of cells is a NOR configuration.

21. (Original) The system of claim 10, wherein the modified flash cells are configured as three-dimensional layers.

22. (Original) The system of claim 21, wherein the three-dimensional layers comprise modified flash cells arranged in a NAND configuration.

23. (Original) The system of claim 21, wherein the three-dimensional layers comprise modified flash cells arranged in a NOR configuration.

24. (Original) The system of claim 10, further comprising an electronic device adapted to house the modified flash cells, the electronic device having an opening to receive the UV light window.

25. (Original) The system of claim 24, wherein the electronic device is a portable electronic device.

26. (Original) The system of claim 25, wherein the portable electronic device is a cellular telephone.

27. (Original) The system of claim 25, wherein the portable electronic device is a personal digital assistant (PDA).

28. (Original) The system of claim 25, wherein the portable electronic device is an MP3 player.

29. (Original) The system of claim 25, wherein the portable electronic device is a lap-top computer.

30-31. (Canceled)

32. (Previously presented) A method comprising:
exposing a two-terminal drain-gate-connected modified flash cell to ultraviolet (UV) light; and
erasing the modified flash cell using the UV light without the use of any erasing circuitry.

33. (Canceled)

34. (Previously presented) A system comprising:
means for exposing a two-terminal drain-gate-connected modified flash cell to ultraviolet (UV) light; and
means for erasing the modified flash cell using the UV light without the use of any erasing circuitry.

35. (Canceled)

36. (Previously presented) A device comprising:
two-terminal drain-gate-connected modified flash cells; and
an ultraviolet (UV) light window adapted to expose the two-terminal drain-gate-connected modified flash cells to UV light.

37. (Previously presented) The device of claim 36, wherein the two-terminal drain-gate-connected modified flash cells are configured as a two-dimensional planar matrix of cells.

38. (Previously presented) The device of claim 37, wherein the two-dimensional planar matrix of cells is a NAND configuration.

39. (Previously presented) The device of claim 37, wherein the two-dimensional planar matrix of cells is a NOR configuration.

40. (Previously presented) The device of claim 36, wherein the two-terminal drain-gate-connected modified flash cells are configured as three-dimensional layers.

41. (Previously presented) A system comprising:
a non-volatile memory; and
an ultraviolet (UV) light window adapted to expose the non-volatile memory to UV light, wherein the UV light window is located below a substrate of the memory.

42. (Previously presented) The system of claim 41, wherein the UV light window is adapted to diffuse UV light entering the UV light window.

43. (Canceled)

44. (Canceled)